SM12GZ47,SM12JZ47,SM12GZ47A,SM12JZ47A

TOSHIBA BI-DIRECTIONAL TRIODE THYRISTOR SILICON PLANAR TYPE

SM12GZ47,SM12JZ47,SM12GZ47A,SM12JZ47A

AC POWER CONTROL APPLICATIONS

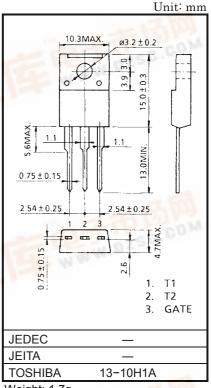
Repetitive Peak off-State Voltage : V_{DRM} = 400, 600V
 R.M.S On-State Current : I_T (RMS) = 12A

• High Commutating (dv / dt)

• Isolation Voltage : $V_{Isol} = 1500V AC$

MAXIMUM RATINGS

CHARACTERI	STIC	SYMBOL	RATING	UNIT	
Repetitive Peak Off-State Voltage and	SM12GZ47 SM12GZ47A	\/··	400	V	
Repetitive Peak Reverse Voltage	SM12JZ47 SM12JZ47A	V_{DRM}	600		
R. M. S. On-tate Currer (Full Sine Waveform TC		I _{T (RMS)}	12	А	
Peak One Cylce Surge	On-State		120 (50Hz)	A	
Current (Non-Repetitive	e)	ITSM	132 (60Hz)		
I ² t Limit Value	E EE	ı ² t	72	A ² s	
Critical Rate of Rise of C Current	On-State (Note 1)	di / dt	50	A / µs	
Peak Gate Power Dissip	ation	P_{GM}	5	W	
Average Gate Power Dis	ssipation	P _{G (AV)}	0.5	W	
Peak Gate Voltage		V_{FGM}	10	V	
Peak Gate Current		I _{GM}	2	Α	
Junction Temperature		Tj	-40~125	°C	
Storage Temperature Ra	ange	T _{stg}	-40~125	°C	
Isolation Voltage (AC, t	= 1min.)	V _{Isol}	1500	V	



Weight: 1.7g

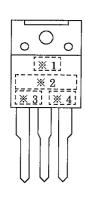
Note 1: di / dt test condition $V_{DRM} = 0.5 \times Rated$ $I_{TM} \le 17A$ $t_{gw} \ge 10 \mu s$ $t_{gr} \le 250 ns$ $i_{gp} = I_{GT} \times 2.0$



ELECTRICAL CHARACTERISTICS (Ta = 25°C)

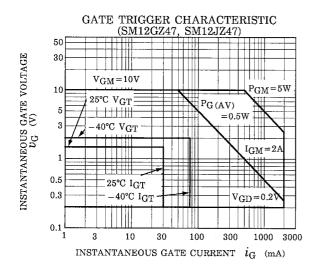
CHARACTERISTIC		SYMBOL	TEST CONDITION		MIN	TYP.	MAX	UNIT		
Repetitive Peak (Off-Sta	te Current		I _{DRM}	V _{DRM} = Rated		_	_	20	μΑ
Gate Trigger Voltage III IV		I	V _{GT}	$V_D = 12V$, $R_L = 20\Omega$	T2 (+) , Gate (+)		_	1.5	V	
		Ш			T2 (+) , Gate (-)	_	_	1.5		
		III			T2 (-) , Gate (-)		_	1.5		
		IV			T2 (-) , Gate (+)		_	_		
			I		$V_D = 12V$, $R_L = 20\Omega$	T2 (+) , Gate (+)	_	_	30	- mA
	SM12	SM12GZ47 SM12JZ47	Ш			T2 (+) , Gate (-)	_	_	30	
Gate Trigger Current SN	SM12		III			T2 (-) , Gate (-)		_	30	
			IV	I _{GT}		T2 (-) , Gate (+)	_	_	_	
		SM12GZ47A SM12JZ47A	I			T2 (+) , Gate (+)	_	_	20	
	SM12		Ш			T2 (+) , Gate (-)	_	_	20	
	SM12		III			T2 (-) , Gate (-)	1	_	20	
			IV			T2 (-) , Gate (+)	_	_	_	
Peak On-State Voltage		V _{TM}	I _{TM} = 17A			_	1.5	V		
Gate Non-Trigger Voltage		V_{GD}	V _D = Rated, Tc = 125°C		0.2	_	_	V		
Holding Current		lΗ	V _D = 12V, I _{TM} = 1A		_	_	50	mA		
Thermal Resistance		R _{th (j-c)}	Junction to Case, AC		_	_	3.0	°C/W		
Critical Rate of Rise of Off-State Voltage	SM12GZ47 SM12JZ47		dv / dt	V _{DRM} = Rated, T _j = 125°C Exponential Rise		l	300	_	- V / µs	
	SM12GZ47 SM12JZ47		uv / ut			_	200	_		
Critical Rate of Rise of Off-State	!	SM12GZ47 SM12JZ47		(dy / dt) o	V _{DRM} = 400V, T _i = 125°C		10	_	_	V/µs
Voltage at Commutation		SM12GZ47 SM12JZ47		(dv / dt) c	(di / dt) c = -6.5A / ms		4		_	v / µs

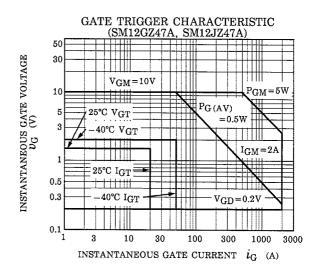
MARKING

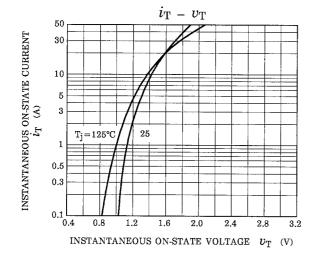


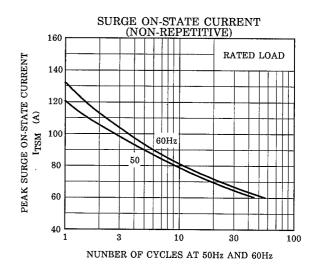
*NUMBER		MARK		
*1	TOSHIBA PRODUCT MARK		5	
*2		SM12GZ47, SM12GZ47A	M12GZ47	
	TYPE	SM12JZ47, SM12JZ47A	M12JZ47	
*3		SM12GZ47A, SM12JZ47A	A	
*4		(Starting from Alphabet A) (Last Decimal Digit of the Current Year)	Example 8A: January 1998 8B: February 1998 8L: December 1998	

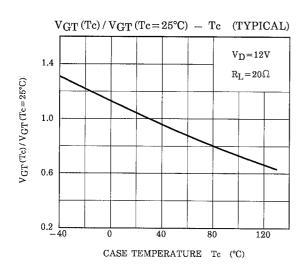
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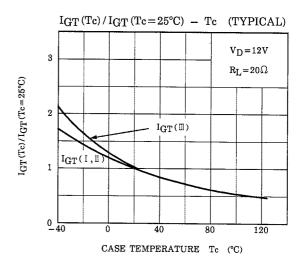




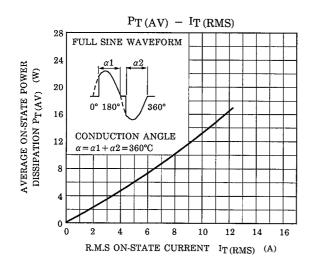


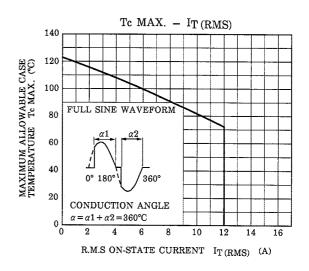


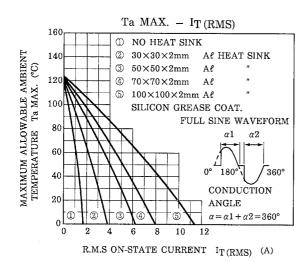


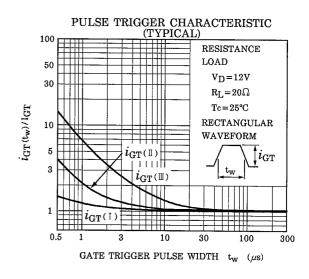


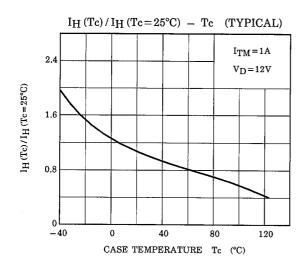
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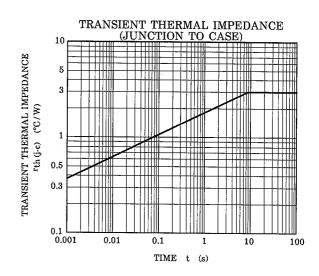












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